

De-Sheng Jiang

List of Publications by Year in descending order

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26
papers

353
citations

933447

10
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794594

19
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26
all docs

26
docs citations

26
times ranked

414
citing authors

#	ARTICLE	IF	CITATIONS
1	Suppression of thermal degradation of InGaN/GaN quantum wells in green laser diode structures during the epitaxial growth. Applied Physics Letters, 2013, 103, .	3.3	68
2	Fabrication of room temperature continuous-wave operation GaN-based ultraviolet laser diodes. Journal of Semiconductors, 2017, 38, 051001.	3.7	48
3	Effects of edge dislocations and intentional Si doping on the electron mobility of n-type GaN films. Applied Physics Letters, 2006, 89, 112106.	3.3	40
4	Investigation on the compensation effect of residual carbon impurities in low temperature grown Mg doped GaN films. Journal of Applied Physics, 2014, 115, 163704.	2.5	35
5	Improvement of characteristics of InGaN-based laser diodes with undoped InGaN upper waveguide layer. Journal of Applied Physics, 2012, 112, .	2.5	25
6	Design Considerations for GaN-Based Blue Laser Diodes With InGaN Upper Waveguide Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1500705-1500705.	2.9	16
7	In situ tuning biexciton antibinding-binding transition and fine-structure splitting through hydrostatic pressure in single InGaAs quantum dots. Europhysics Letters, 2014, 107, 27008.	2.0	13
8	Unintentionally doped semi-insulating GaN with a low dislocation density grown by metalorganic chemical vapor deposition. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 051207.	1.2	13
9	Effects of thin heavily Mg-doped GaN capping layer on ohmic contact formation of p-type GaN. Semiconductor Science and Technology, 2013, 28, 105020.	2.0	11
10	The significant effect of the thickness of Ni film on the performance of the Ni/Au Ohmic contact to p-GaN. Journal of Applied Physics, 2014, 116, .	2.5	11
11	Performance comparison of front- and back-illuminated modes of the AlGaIn-based p-i-n solar-blind ultraviolet photodetectors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 031204.	1.2	9
12	Single-Photon Emission from GaAs Quantum Dots Embedded in Nanowires. Chinese Physics Letters, 2015, 32, 077804.	3.3	9
13	Utilization of polarization-inverted AlInGaIn or relatively thinner AlGaIn electron blocking layer in InGaIn-based blue-violet laser diodes. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 011209.	1.2	8
14	Different variation behaviors of resistivity for high-temperature-grown and low-temperature-grown p-GaN films. Chinese Physics B, 2016, 25, 027102.	1.4	7
15	New design of upper waveguide with unintentionally doped InGaIn layer for InGaIn-based laser diode. Optics and Laser Technology, 2017, 97, 284-289.	4.6	7
16	Coupling and single-photon purity of a quantum dot-cavity system studied using hydrostatic pressure. Journal of Applied Physics, 2015, 117, 014304.	2.5	6
17	The thickness design of unintentionally doped GaIn interlayer matched with background doping level for InGaIn-based laser diodes. AIP Advances, 2016, 6, 035124.	1.3	6
18	1.3 μm single-photon emission from strain-coupled bilayer of InAs/GaAs quantum dots at the temperature up to 120 K. Applied Physics Letters, 2017, 111, .	3.3	6

#	ARTICLE	IF	CITATIONS
19	Tuning exciton energy and fine-structure splitting in single InAs quantum dots by applying uniaxial stress. AIP Advances, 2016, 6, .	1.3	5
20	Influence of residual carbon impurities in i-GaN layer on the performance of GaN-based p-i-n photodetectors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 011204.	1.2	4
21	Different influences of u-InGaN upper waveguide on the performance of GaN-based blue and green laser diodes. Chinese Physics B, 2017, 26, 114203.	1.4	2
22	Resistivity reduction of low temperature grown p-Al _{0.09} Ga _{0.91} N by suppressing the incorporation of carbon impurity. AIP Advances, 2018, 8, 085005.	1.3	2
23	Investigation of breakdown mechanism during field emission process of AlN thin film microscopic cold cathode. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 012201.	1.2	1
24	Deep levels induced optical memory effect in thin InGaN film. AIP Advances, 2018, 8, 085222.	1.3	1
25	Observation of negative differential resistance in GaN-based multiple-quantum-well light-emitting diodes. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 011206.	1.2	0
26	Electroluminescence property improvement by adjusting quantum wells' position relative to p-doped region in InGaN/GaN multiple-quantum-well light emitting diodes. AIP Advances, 2017, 7, 035103.	1.3	0